

CLAIM AMENDMENTS

1. (Currently Amended) ~~A high-frequency~~ An integrated circuit device comprising:
a semiconductor amplification element; and
a bias circuit for applying a bias voltage to the semiconductor amplification element,
wherein a power source of the bias circuit is connected to a power source of the semiconductor
amplification element via a semiconductor element such that idle current of the semiconductor
amplification element ~~can be~~ is changed in response to change of a supply voltage of the
semiconductor amplification element.
2. (Currently Amended) The ~~high-frequency~~ integrated circuit device according to
Claim 1, wherein the semiconductor element is a transistor.
3. (Currently Amended) The ~~high-frequency~~ integrated circuit device according to
Claim 1, wherein the semiconductor element is a diode.
4. (Currently Amended) The ~~high-frequency~~ integrated circuit device according to
Claim 1, which acts as a power amplifier circuit including a ~~high-frequency~~ transistor as the
semiconductor amplification element, wherein the bias circuit includes a bias generating circuit
for generating a base bias of the ~~high-frequency~~ transistor and a temperature compensation
circuit for ~~performing~~ temperature compensation of the bias generating circuit.